

containing as a main constituting element at least one element selected from the group consisting of rhodium, ruthenium, iridium, osmium, and platinum, and as an adding element at least one element selected from the group consisting of nickel and titanium in an amount of 10 atom % or more.

C1
Wnt

2. (Amended) A semiconductor device equipped with a capacitor for storing information comprising a substrate, a first capacitor electrode formed on the substrate, an oxide film formed in contact with the first capacitor electrode, a second capacitor electrode formed in contact with the oxide film, and an insulating film containing silicon as a main constituting element and formed in contact with the first capacitor electrode or the second capacitor electrode, said first capacitor electrode or said second capacitor electrode which is in contact with the insulating film containing as a main constituting element ruthenium, and as an adding element at least one element selected from the group consisting of nickel and titanium in an amount of 10 atom % or more.

C2
Wnt

3. (Amended) A semiconductor device equipped with a capacitor for storing information comprising a substrate, a first capacitor electrode formed on the substrate, an oxide film formed in contact with the first capacitor electrode, a second capacitor electrode formed in contact with the oxide film, and an insulating film containing silicon as a main constituting element and formed in contact with the first capacitor electrode or the second capacitor electrode, said first capacitor electrode or said second capacitor electrode which is in contact with the insulating film containing as a main constituting element ruthenium, and as an adding element titanium in an amount of 10 atom % or more.

4. (Amended) A semiconductor device equipped with a capacitor for storing information comprising a substrate, a first capacitor electrode formed on the substrate, an oxide film formed in contact with the first capacitor electrode, a second

capacitor electrode formed in contact with the oxide film, and an insulating film containing silicon as a main constituting element and formed in contact with the first capacitor electrode or the second capacitor electrode, said first capacitor electrode or said second capacitor electrode which is in contact with the insulating film containing as a main constituting element ruthenium, and as an adding element nickel.

CB Cond
5. (Amended) A semiconductor device equipped with a capacitor for storing information comprising a substrate, a first capacitor electrode formed on the substrate, an oxide film formed in contact with the first capacitor electrode, a second capacitor electrode formed in contact with the oxide film, and an insulating film containing silicon as a main constituting element and formed in contact with the first capacitor electrode or the second capacitor electrode, said first capacitor electrode or said second capacitor electrode which is in contact with the insulating film containing as a main constituting material at least one material selected from ruthenium oxide and iridium oxide, and as an adding element at least one element selected from the group consisting of palladium, nickel, cobalt, and titanium.

CB Oxid
14. (Amended) A process for producing a semiconductor device equipped with a capacitor for storing information comprising a substrate, a first capacitor electrode formed on the substrate, an oxide film for a dielectric formed in contact with the first capacitor electrode, a second capacitor electrode formed in contact with the oxide film, and an insulating film containing silicon as a main constituting element and formed in contact with the first capacitor electrode or the second capacitor electrode, which comprises forming the first capacitor electrode or the second capacitor electrode which is in contact with the insulating film by using

- (a) at least one element selected from the group consisting of rhodium, ruthenium, iridium, osmium and platinum as a main constituting element, or
- (b) at least one material selected from the group consisting of

C3
Con'd

ruthenium oxide and iridium oxide as a main constituting material, and at least one element selected from the group consisting of nickel and titanium as an adding element in an amount of 10 atom % or more.

C3
Con'd

15. (Amended) A process for producing a semiconductor device equipped with a capacitor for storing information comprising an oxide film formed between a first capacitor electrode and a second capacitor electrode, and an insulating film containing silicon as a main constituting element being formed for insulating one of the first capacitor electrode or the second capacitor electrode, which comprises forming an electroconductive film containing as a main constituting element at least one element selected from the group consisting of palladium, nickel, cobalt and titanium between said one of the first capacitor electrode or the second capacitor electrode and the insulating film.

C3

17. (Amended) A semiconductor device equipped with a capacitor for storing information comprising a substrate, a first capacitor electrode formed on the substrate, an oxide film formed in contact with the first capacitor electrode, a second capacitor electrode formed in contact with the oxide film, and an insulating film containing silicon as a main constituting element and formed in contact with the first capacitor electrode or the second capacitor electrode, said first capacitor electrode or said second capacitor electrode which is in contact with the insulating film containing as a main constituting element at least one element selected from the group consisting of rhodium, ruthenium, iridium, osmium, and platinum, and means for enhancing adhesiveness of said first or said second capacitor electrode to said insulating film to prevent peeling comprising providing as an adding element to said first or second capacitor electrode at least one element selected from the group consisting of nickel and titanium. --
